

CORRIGENDUM

Corrigendum: Self-induced growth of vertical GaN nanowires on silica (2015 *Nanotechnology* [27](#) [135602](#))

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Corrigendum: Self-induced growth of vertical GaN nanowires on silica (2015 *Nanotechnology* 27 135602)

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In the published article, the statement referring to [17] on page 5 does not correspond to the exact content of Sobanska's publication and should read.

Sobanska *et al* [17] compared the nucleation of GaN NWs on crystalline sapphire and on amorphous alumina. These authors observed dense arrays of NWs on the amorphous surface, while a rough compact layer was formed on sapphire, i.e. the NW formation was more favourable on the amorphous

layer. This result contrasts with our study where the crystalline order at the Si surface seems to help NW nucleation.

The correct reference [17] is:

Sobanska M, Klosek K, Borysiuk J, Kret S, Tchutchulashvili G, Gieraltowska S and Zytkeiwicz Z R 2014 Enhanced catalyst-free nucleation of GaN nanowires on amorphous Al₂O₃ by plasma-assisted molecular beam epitaxy *J. Appl. Phys.* **115** 043517